

METHODS OF BASE FORMATION IN A BiCMOS PROCESS

Abstract

Methods for fabricating a heterojunction bipolar transistor having a raised extrinsic base is provided in which the base resistance is reduced by forming a silicide atop the raised extrinsic base that extends to the emitter region in a self-aligned manner. The silicide formation is incorporated into a BiCMOS process flow after the raised extrinsic base has been formed. The present invention also provides a heterojunction bipolar transistor having a raised extrinsic base and a silicide located atop the raised extrinsic base. The silicide atop the raised extrinsic base extends to the emitter in a self-aligned manner. The emitter is separated from the silicide by a spacer.